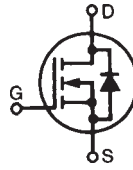


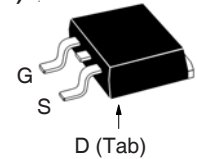
**X-Class
Power MOSFET**
**IXTA20N65X
IXTP20N65X
IXTH20N65X**
 $V_{DSS} = 650V$
 $I_{D25} = 20A$
 $R_{DS(on)} \leq 210m\Omega$

N-Channel Enhancement Mode

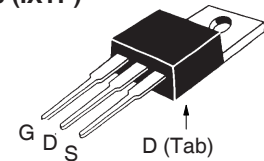


| Symbol | Test Conditions | Maximum Ratings | |
|---------------|---|-------------------|------------|
| V_{DSS} | $T_J = 25^\circ C$ to $150^\circ C$ | 650 | V |
| V_{DGR} | $T_J = 25^\circ C$ to $150^\circ C$, $R_{GS} = 1M\Omega$ | 650 | V |
| V_{GSS} | Continuous | ± 30 | V |
| V_{GSM} | Transient | ± 40 | V |
| I_{D25} | $T_C = 25^\circ C$ | 20 | A |
| I_{DM} | $T_C = 25^\circ C$, Pulse Width Limited by T_{JM} | 40 | A |
| dv/dt | $I_S \leq I_{D25}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ C$ | 30 | V/ns |
| P_D | $T_C = 25^\circ C$ | 320 | W |
| T_J | | -55 ... +150 | $^\circ C$ |
| T_{JM} | | 150 | $^\circ C$ |
| T_{stg} | | -55 ... +150 | $^\circ C$ |
| T_L | Maximum Lead Temperature for Soldering | 300 | $^\circ C$ |
| T_{SOLD} | 1.6 mm (0.062in.) from Case for 10s | 260 | $^\circ C$ |
| F_C | Mounting Force (TO-263) | 10.65 / 2.2..14.6 | N/lb |
| M_d | Mounting Torque (TO-220 & TO-247) | 1.13 / 10 | Nm/lb.in |
| Weight | TO-263 | 2.5 | g |
| | TO-220 | 3.0 | g |
| | TO-247 | 6.0 | g |

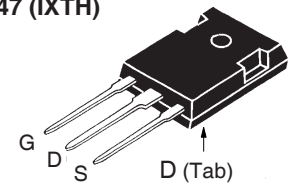
TO-263 (IXTA)



TO-220 (IXTP)



TO-247 (IXTH)



G = Gate D = Drain
S = Source Tab = Drain

Features

- International Standard Packages
- Low $R_{DS(ON)}$ and Q_G
- Low Package Inductance

Advantages

- High Power Density
- Easy to Mount
- Space Savings

Applications

- Switch-Mode and Resonant-Mode Power Supplies
- DC-DC Converters
- PFC Circuits
- AC and DC Motor Drives
- Robotics and Servo Controls

| Symbol | Test Conditions ($T_J = 25^\circ C$, Unless Otherwise Specified) | Characteristic Values | | |
|--------------|---|-----------------------|------|-------------------------|
| | | Min. | Typ. | Max. |
| BV_{DSS} | $V_{GS} = 0V$, $I_D = 250\mu A$ | 650 | | V |
| $V_{GS(th)}$ | $V_{DS} = V_{GS}$, $I_D = 250\mu A$ | 3.0 | | 5.5 V |
| I_{GSS} | $V_{GS} = \pm 30V$, $V_{DS} = 0V$ | | | ± 100 nA |
| I_{DSS} | $V_{DS} = V_{DSS}$, $V_{GS} = 0V$ $T_J = 125^\circ C$ | | | 5 μA 50 μA |
| $R_{DS(on)}$ | $V_{GS} = 10V$, $I_D = 0.5 \cdot I_{D25}$, Note 1 | | | 210 m Ω |

| Symbol | Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified) | Characteristic Values | | |
|-------------------------------------|--|--|------|-------------------------|
| | | Min. | Typ. | Max |
| g_{fs} | $V_{DS} = 10\text{V}$, $I_D = 0.5 \cdot I_{D25}$, Note 1 | 9 | 15 | S |
| R_{Gi} | Gate Input Resistance | | 3.4 | Ω |
| C_{iss} | $V_{GS} = 0\text{V}$, $V_{DS} = 25\text{V}$, $f = 1\text{MHz}$ | | 1390 | pF |
| C_{oss} | | | 1060 | pF |
| C_{rss} | | | 22 | pF |
| Effective Output Capacitance | | | | |
| $C_{o(er)}$ | Energy related | $V_{GS} = 0\text{V}$ $V_{DS} = 0.8 \cdot V_{DSS}$ | 77 | pF |
| $C_{o(tr)}$ | Time related | | 232 | pF |
| Resistive Switching Times | | | | |
| $t_{d(on)}$ | $V_{GS} = 10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 0.5 \cdot I_{D25}$ $R_G = 5\Omega$ (External) | | 18 | ns |
| t_r | | | 30 | ns |
| $t_{d(off)}$ | | | 46 | ns |
| t_f | | | 22 | ns |
| $Q_{g(on)}$ | $V_{GS} = 10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 0.5 \cdot I_{D25}$ | | 35 | nC |
| Q_{gs} | | | 7 | nC |
| Q_{gd} | | | 18 | nC |
| R_{thJC} | | | | 0.39 $^\circ\text{C/W}$ |
| R_{thCS} | TO-220 | | 0.50 | $^\circ\text{C/W}$ |
| | TO-247 | | 0.21 | $^\circ\text{C/W}$ |

Source-Drain Diode

| Symbol | Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified) | Characteristic Values | | |
|----------|--|-----------------------|------|---------------|
| | | Min. | Typ. | Max |
| I_S | $V_{GS} = 0\text{V}$ | | | 20 A |
| I_{SM} | Repetitive, pulse Width Limited by T_{JM} | | | 80 A |
| V_{SD} | $I_F = I_S$, $V_{GS} = 0\text{V}$, Note 1 | | | 1.4 V |
| t_{rr} | $I_F = 10\text{A}$, $-di/dt = 100\text{A}/\mu\text{s}$ $V_R = 100\text{V}$ | | 350 | ns |
| Q_{RM} | | | 4.45 | μC |
| I_{RM} | | | 25 | A |

Note 1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.

PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

| | | | | | | | | | | |
|--|-----------|-----------|-----------|-----------|-------------|-------------|-------------|-------------|-------------|-------------|
| IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: | 4,835,592 | 4,931,844 | 5,049,961 | 5,237,481 | 6,162,665 | 6,404,065B1 | 6,683,344 | 6,727,585 | 7,005,734B2 | 7,157,338B2 |
| | 4,860,072 | 5,017,508 | 5,063,307 | 5,381,025 | 6,259,123B1 | 6,534,343 | 6,710,405B2 | 6,759,692 | 7,063,975B2 | |
| | 4,881,106 | 5,034,796 | 5,187,117 | 5,486,715 | 6,306,728B1 | 6,583,505 | 6,710,463 | 6,771,478B2 | 7,071,537 | |

Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

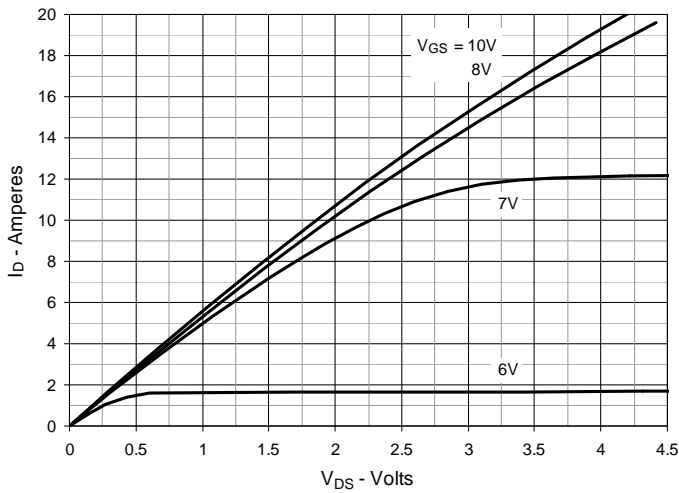


Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

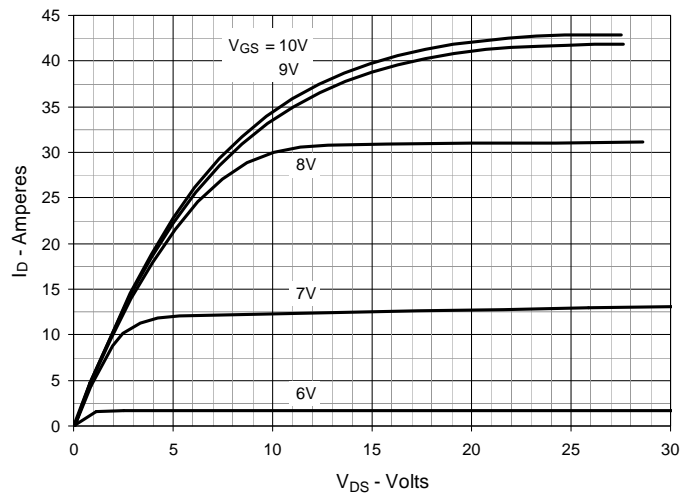


Fig. 3. Output Characteristics @ $T_J = 125^\circ\text{C}$

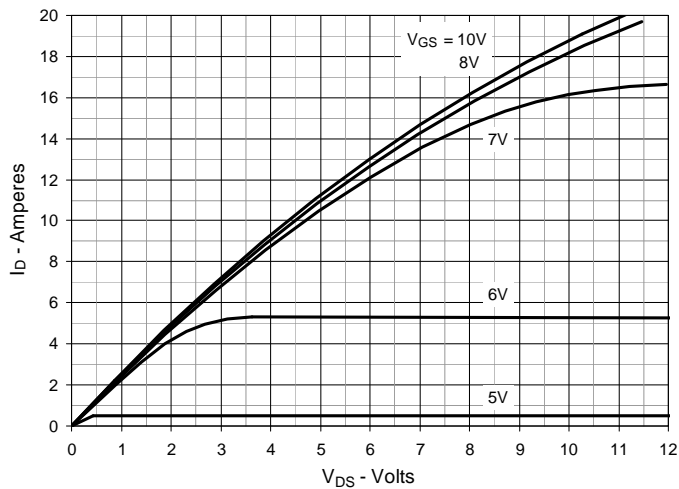


Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 10\text{A}$ Value vs. Junction Temperature

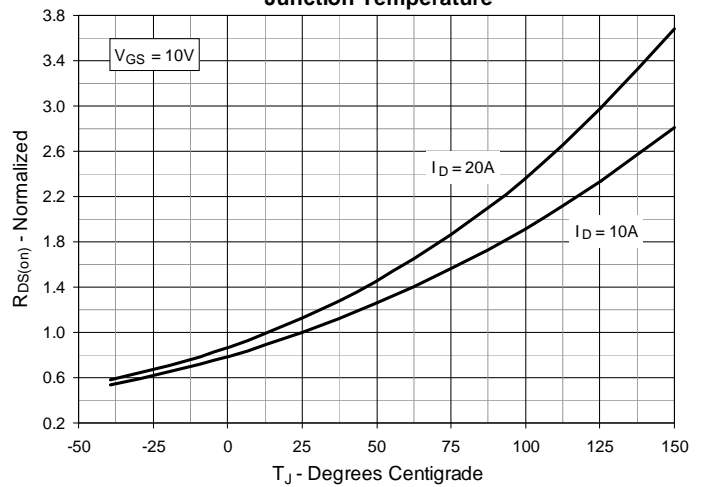


Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 10\text{A}$ Value vs. Drain Current

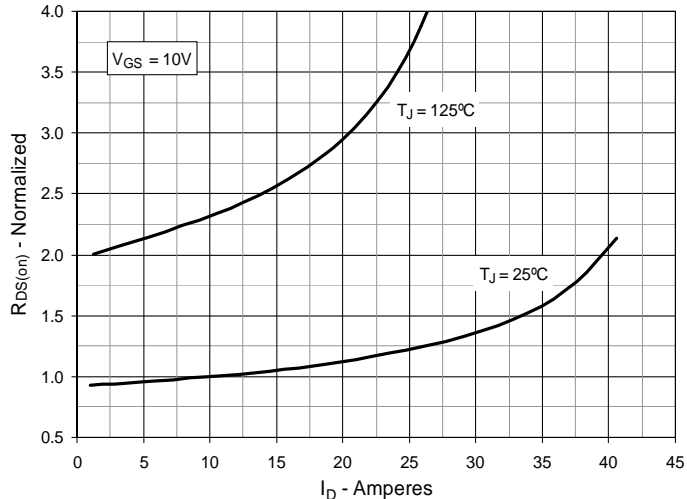


Fig. 6. Normalized Breakdown & Threshold Voltages vs. Junction Temperature

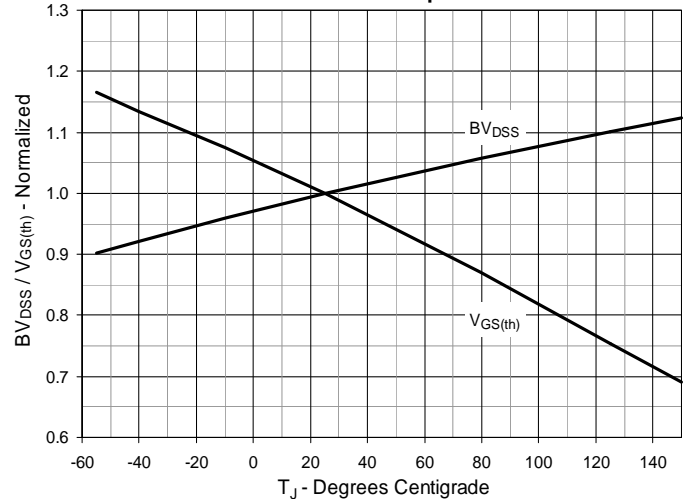


Fig. 7. Maximum Drain Current vs. Case Temperature

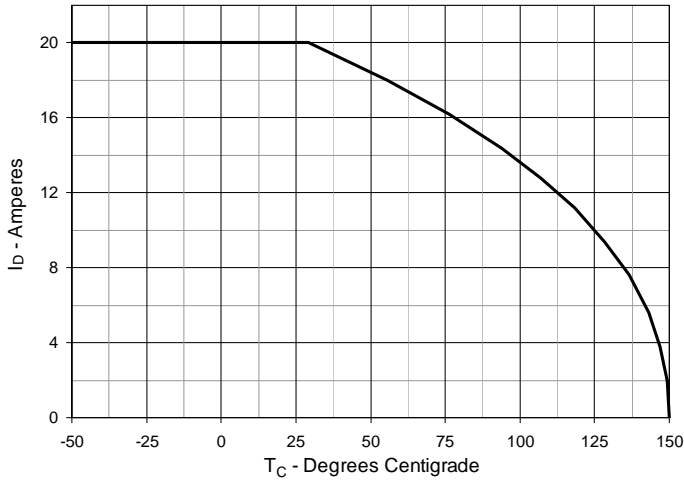


Fig. 8. Input Admittance

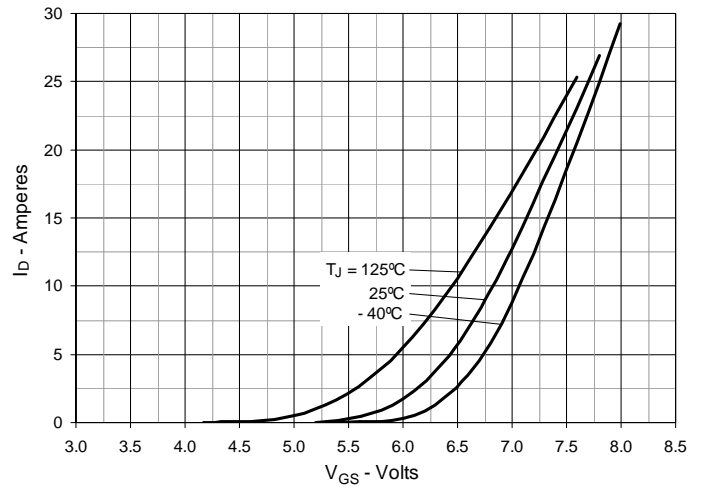


Fig. 9. Transconductance

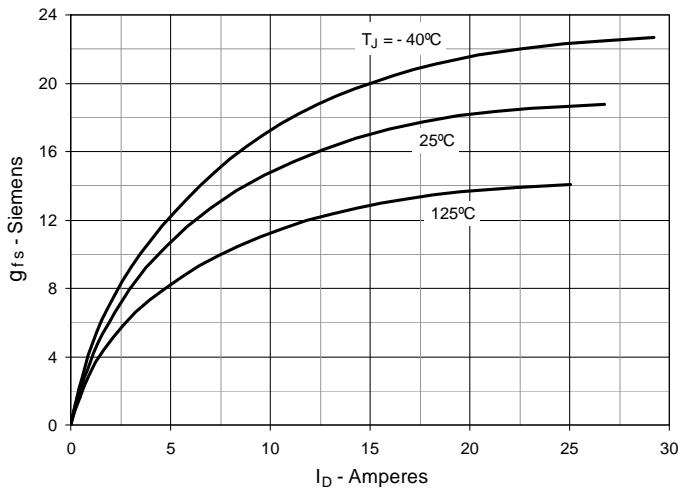


Fig. 10. Forward Voltage Drop of Intrinsic Diode

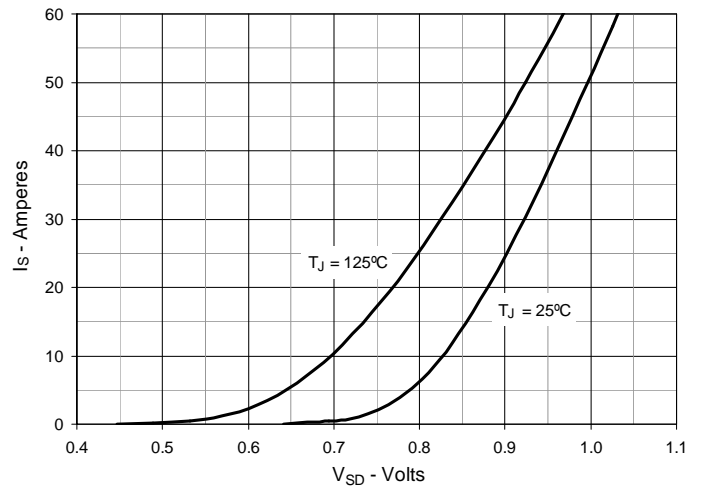


Fig. 11. Gate Charge

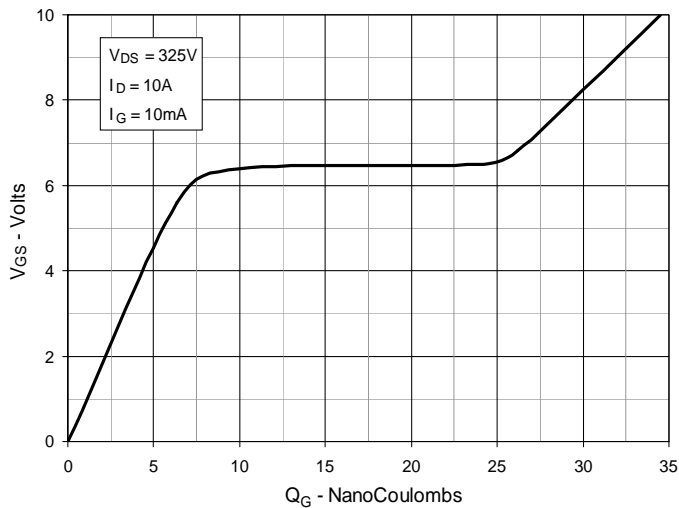


Fig. 12. Capacitance

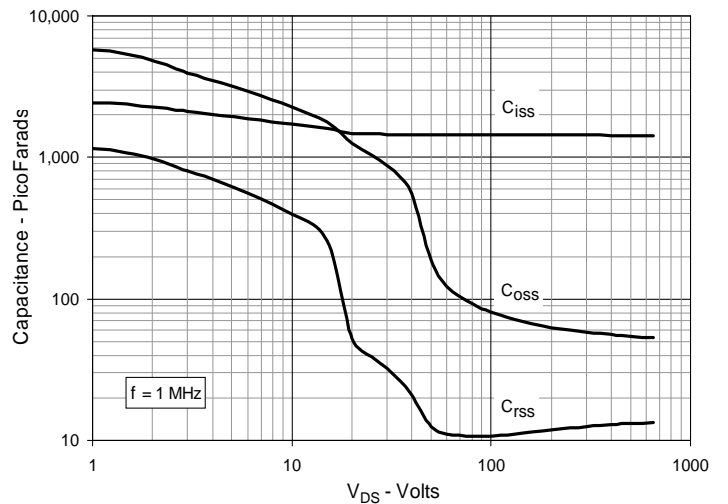


Fig. 13. Output Capacitance Stored Energy

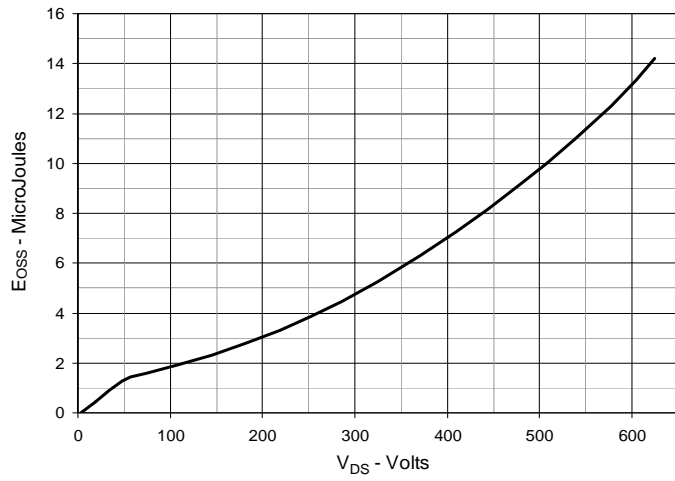


Fig. 14. Forward-Bias Safe Operating Area

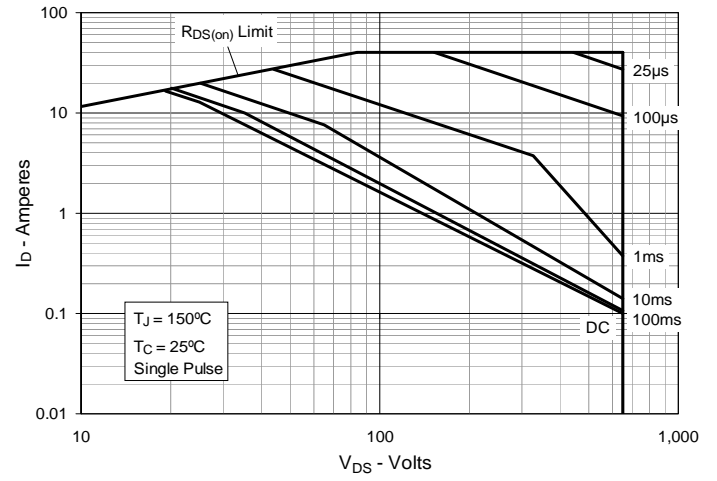
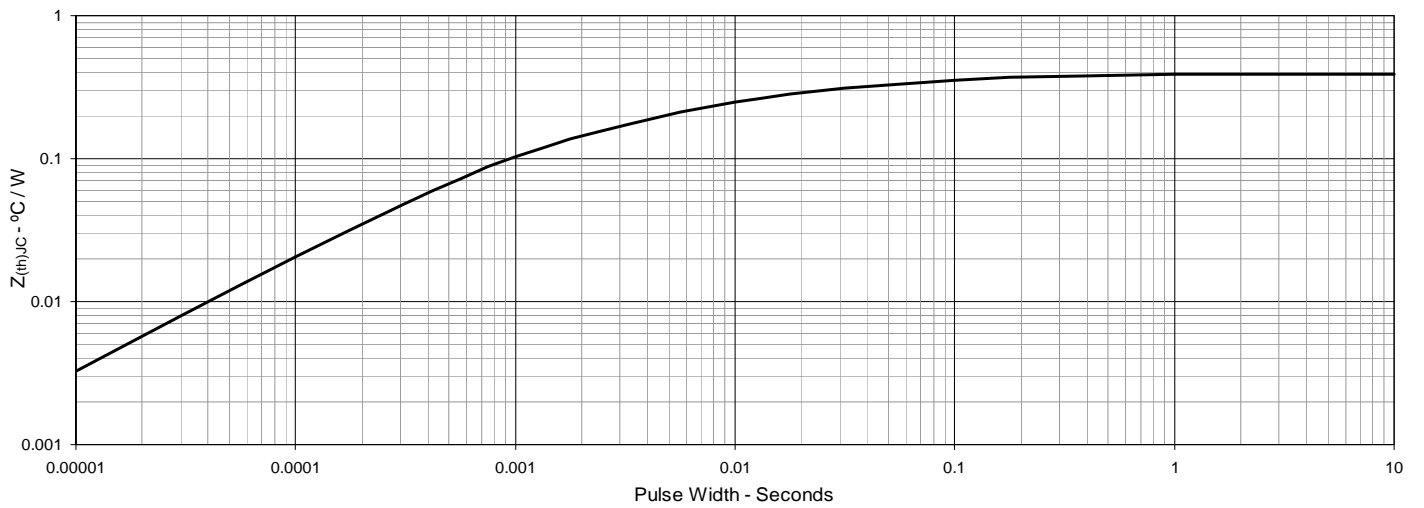


Fig. 15. Maximum Transient Thermal Impedance



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